

Supplementary Material

A comprehensive study on low temperature sintering and microwave/terahertz dielectric properties of BaO-P₂O₅ binary ceramics

Chang-Hao Wang,¹ Kai-Heng Zhang,¹ Wei Wang,¹ Jian Bao,¹ Jia-Pei Jiang,¹ Ke-Hong Zhou,² Jun Li,² Chao Liang,² Da-Wei Liu,¹ Moustafa Adel Darwish,³ Tao Zhou,⁴ Di-Ming Xu,¹ Song Xia,¹ Kar Ban Tan,⁵ and Di Zhou*¹

¹Key Laboratory of Multifunctional Materials and Structures, Ministry of Education, School of Electronic Science and Engineering, Xi'an Jiaotong University, Xi'an, Shaanxi, China

²Chengdu 899 Technology Co., Ltd, Chengdu, Sichuan, China

³Physics Department, Faculty of Science, Tanta University, Al-Geish st., Tanta 31527, Egypt

⁴School of Electronic and Information Engineering, Hangzhou Dianzi University, Hangzhou, 310018, China

⁵Department of Chemistry, Faculty of Science, Universiti Putra Malaysia, Serdang, Selangor, 43400, Malaysia

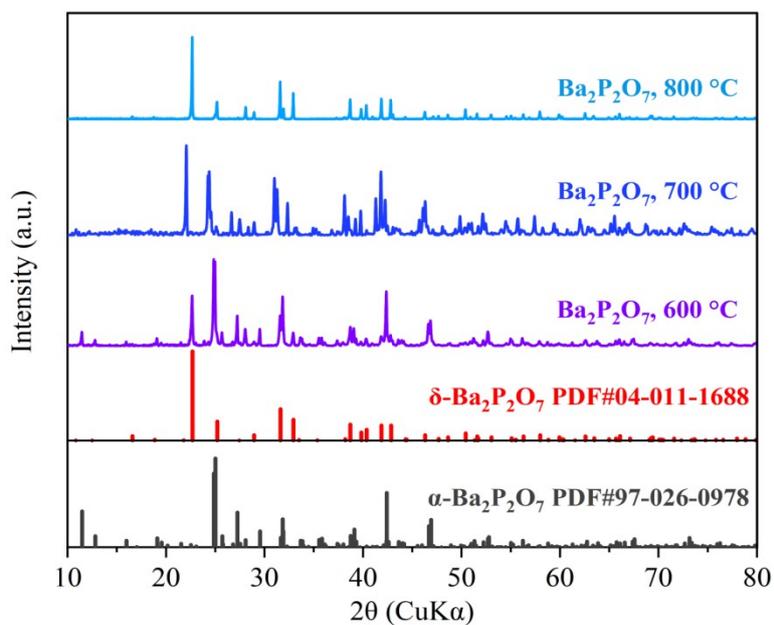


Fig. S1 XRD patterns of $\text{Ba}_2\text{P}_2\text{O}_7$ calcined at 600 °C, 700 °C, 800 °C for 4 h, respectively.

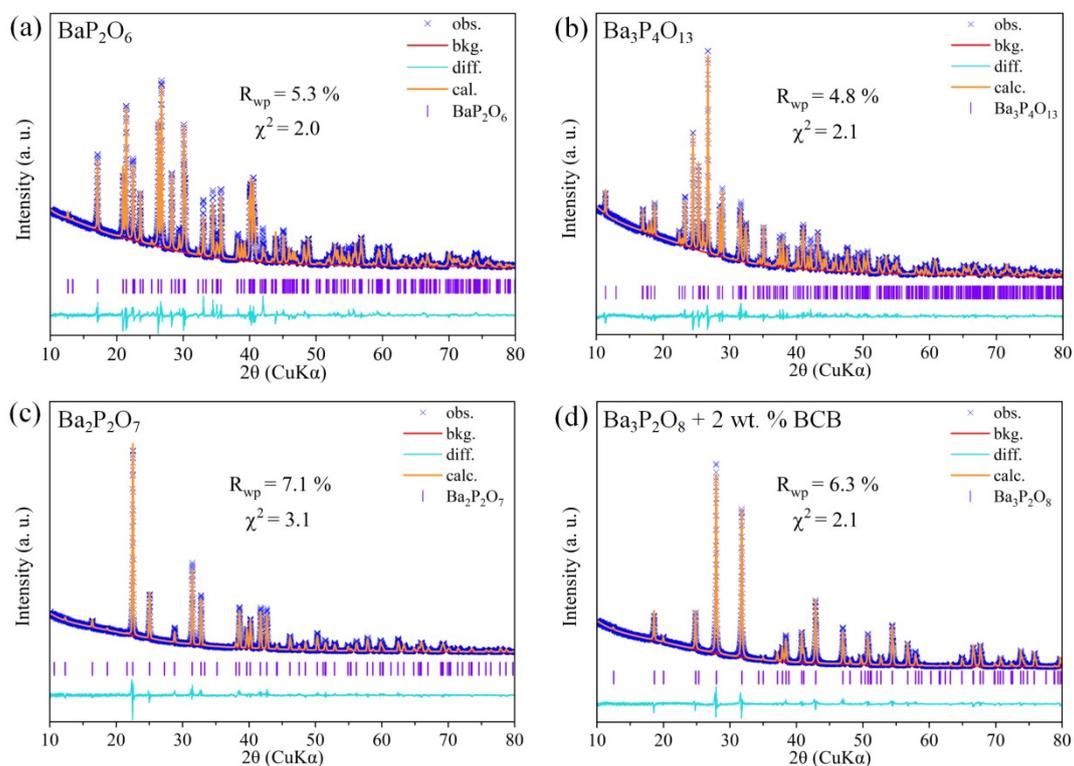


Fig. S2 Rietveld refinement pattern of (a) BaP_2O_6 , (b) $\text{Ba}_3\text{P}_4\text{O}_{13}$, (c) $\text{Ba}_2\text{P}_2\text{O}_7$ and (d) $\text{Ba}_3\text{P}_2\text{O}_8 + 2 \text{ wt. \% BCB}$ sintered at their respective optimal sintering temperatures.

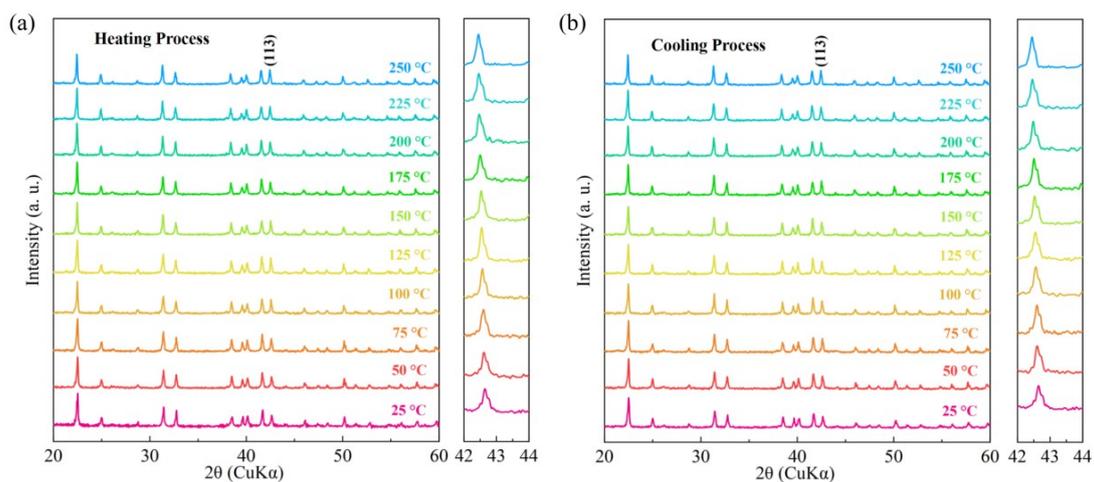


Fig. S3 In situ high-temperature XRD patterns and disparity in (113) X-ray diffraction peaks for $\text{Ba}_2\text{P}_2\text{O}_7$ sintered at $1100\text{ }^\circ\text{C}$: (a) heating process, (b) cooling process.

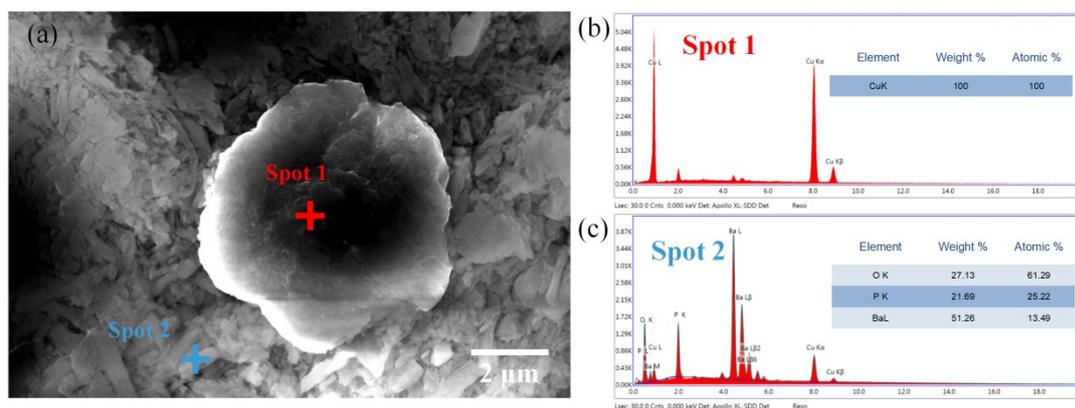


Fig. S4. The BSE and EDS results for BaP_2O_6 ceramics co-fired with Cu powders

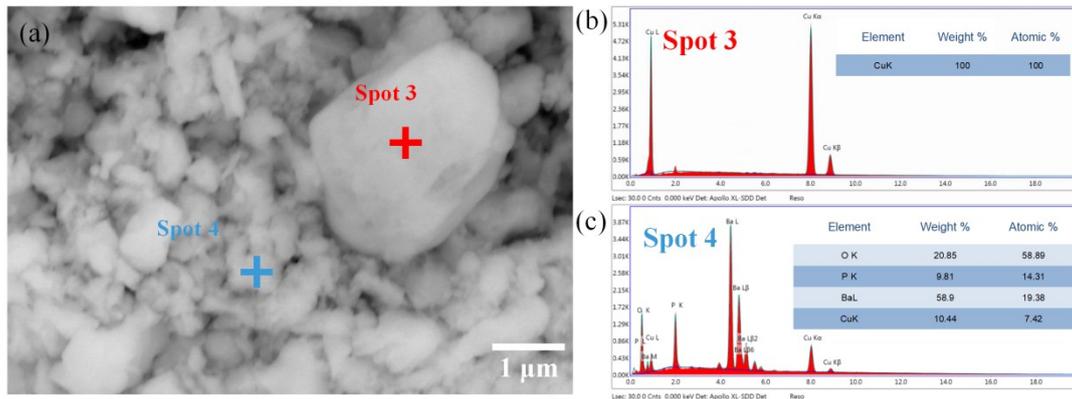


Fig. S5 The BSE and EDS results for $\text{Ba}_3\text{P}_2\text{O}_8 + 2 \text{ wt. } \% \text{ BCB}$ ceramics co-fired with Cu powders.

Table S1 Lattice parameters and refinement result of BaP_2O_6 ceramic sintered at 800 °C.

Atom	x	y	z
Ba1	0.2635(1)	0.1252(6)	0.1982(3)
P1	0.7176(1)	0.3534(8)	0.2225(4)
P2	0.2234(1)	0.4037(7)	0.4272(1)
O1	0.3933(5)	0.3467(2)	0.2674(1)
O2	0.9038(8)	0.3667(2)	0.3953(2)
O3	0.6910(4)	0.4383(1)	0.1392(4)
O4	0.8194(4)	0.2405(3)	0.1290(4)
O5	0.7385(3)	0.0124(2)	0.1213(2)
O6	0.8118(6)	0.1244(1)	0.3860(4)

$$a = 4.5001(2) \text{ \AA}, b = 13.3981(9) \text{ \AA}, c = 8.3419(5) \text{ \AA}, V = 502.95(4) \text{ \AA}^3, R_{\text{wp}} = 5.3 \%, \chi^2 = 2.0$$

Table S2 Lattice parameters and refinement result of Ba₃P₄O₁₃ ceramic sintered at 840 °C.

Atom	<i>x</i>	<i>y</i>	<i>z</i>
Ba1	0	0	0
Ba2	0.6475(4)	-0.4135(8)	0.2275(4)
P1	-0.0005(7)	0.2050(2)	-0.4610(8)
P2	0.3427(7)	0.1902(6)	0.1939(4)
O1	0.0847(2)	0.3063(1)	0.1161(1)
O2	0.5292(2)	0.2939(2)	0.1395(1)
O3	0.2469(1)	0.2337(1)	0.4015(1)
O4	0.4143(1)	-0.0319(1)	0.1835(1)
O5	-0.0241(5)	0.2501(4)	-0.3112(3)
O6	0.0937(5)	0.1805(4)	-0.3001(3)
O7	-0.2677(5)	0.2893(4)	0.4585(3)
O8	-0.2313(5)	0.3628(4)	-0.5113(3)
O9	-0.0901(4)	0.0536(4)	0.4597(28)

$a = 5.6909(1) \text{ \AA}$, $b = 7.2411(7) \text{ \AA}$, $c = 8.0137(5) \text{ \AA}$, $\alpha = 83.6186(3)^\circ$, $\beta = 75.9522(5)^\circ$,
 $\gamma = 70.4811(7)^\circ$, $V=301.78(2) \text{ \AA}^3$, $R_{\text{wp}} = 4.8 \%$, $\chi^2 = 2.1$

Table S3 Lattice parameters and refinement result of Ba₂P₂O₇ ceramic sintered at 1100 °C.

Atom	<i>x</i>	<i>y</i>	<i>z</i>
Ba1	0.3819(2)	0.3819(2)	1/2
Ba2	0.2896(2)	0	0
P1	0	0	0.3005(8)
P2	2/3	1/3	0.2242(1)
O1	0.8520(5)	0	0.2618(1)
O2	0.5123(8)	0.1849(2)	0.3103(5)
O3	-0.0465(5)	0	1/2
O4	0.3117(1)	0.5628(2)	0

$a = 9.4065(3) \text{ \AA}$, $c = 7.0728(2) \text{ \AA}$, $V = 541.97(5) \text{ \AA}^3$, $R_{\text{wp}} = 7.1 \%$, $\chi^2 = 3.1$

Table S4 Lattice parameters and refinement result of Ba₃P₂O₈ + 2 wt. % BCB ceramic sintered at 800 °C.

Atom	<i>x</i>	<i>y</i>	<i>z</i>
Ba1	0	0	0.4052(9)
Ba2	0	0	0
P1	0	0	0.2094(6)
O1	0	0	0.3359(1)
O2	0.8460(5)	0.1539(5)	0.4331(2)

$a = 5.5968(5) \text{ \AA}$, $c = 20.9700(2) \text{ \AA}$, $V = 568.87(5) \text{ \AA}^3$, $R_{\text{wp}} = 6.3 \%$, $\chi^2 = 2.1$

Table S5 Phonon parameters determined from FTIR for Ba₃P₂O₈ ceramic. ($\Delta\epsilon_j$ is the contribution of the j -th oscillator to the static permittivity)

Modes	Ba ₃ P ₂ O ₈				
	ω_{oj}	ω_{pj}	γ_j	S_j	$\Delta\epsilon_j$
1	77.468	80.843	6.5941	1.09	0.0851
2	136.93	223.48	12.505	2.66	0.0913
3	155.48	59.64	8.5312	0.147	0.0549
4	199.79	245.75	14.262	1.51	0.0714
5	227.75	88.196	57.809	0.15	0.254
6	554.34	267.51	6.8391	0.233	0.0123
7	927.3	64.479	4.8753	0.00484	0.00526
8	996.64	439.19	16.364	0.194	0.0164
9	1008.9	355.71	27.387	0.124	0.0271
10	1014	285.79	40.6	0.0794	0.04
11	1089	131.04	32.33	0.0145	0.0297
12	1100.8	101.76	222.82	0.00855	0.202
	$\epsilon_{\infty} = 2.78$			$\epsilon_0 = 9.00$	

Table S6. Phonon parameters determined from FTIR for Ba₃P₂O₈ + 2 wt. % BCB ceramic.

Modes	Ba ₃ P ₂ O ₈ + 2 wt. % BCB				
	ω_{oj}	ω_{pj}	γ_j	S_j	$\Delta\epsilon_j$
1	77.458	62.63	6.5485	0.654	0.0845
2	132.17	69.019	4.5943	0.273	0.0348
3	140.85	177.24	15.829	1.58	0.112
4	180.29	35.22	7.0113	0.0382	0.0389
5	204.82	189.89	11.43	0.859	0.0558
6	217.53	164.81	45.046	0.574	0.207
7	555.38	247.09	7.2396	0.198	0.013
8	927.51	48.985	3.9837	0.00279	0.0043
9	991.33	350.09	13.662	0.125	0.0138
10	1003.8	373.4	19.418	0.138	0.0193
11	1021.4	279.82	26.041	0.0751	0.0255
12	1059.7	95.182	34.019	0.00807	0.0321
13	1086.4	99.609	24.757	0.00841	0.0228
	$\epsilon_\infty = 2.65$		$\epsilon_0 = 7.18$		

Table S7 Comparisons of dielectric properties determined by THz-TDS and AVNA for BaP₂O₆ ceramic.

Methods	BaP ₂ O ₆			
	ϵ'	ϵ''	$\tan\delta$	$Q \times f$ (GHz)
THz-TDS (@ 1 THz)	5.88	1.89×10^{-1}	3.21×10^{-2}	3.12×10^4
AVNA (@ 12.72 GHz)	6.23	4.63×10^{-3}	7.44×10^{-4}	1.71×10^4

Table S8 Comparisons of dielectric properties determined by THz-TDS and AVNA for Ba₃P₄O₁₃ ceramic.

Methods	Ba ₃ P ₄ O ₁₃			
	ϵ'	ϵ''	$\tan\delta$	$Q \times f$ (GHz)
THz-TDS (@ 1 THz)	7.69	9.89×10^{-1}	1.29×10^{-1}	7.75×10^3
AVNA (@ 11.18 GHz)	7.70	6.06×10^{-3}	7.87×10^{-4}	1.42×10^4

Table S9 Comparisons of dielectric properties determined by THz-TDS and AVNA for Ba₂P₂O₇ ceramic.

Methods	Ba ₂ P ₂ O ₇			
	ϵ'	ϵ''	$\tan\delta$	$Q \times f$ (GHz)
THz-TDS (@ 1 THz)	7.65	8.82×10^{-1}	1.15×10^{-1}	8.70×10^3
AVNA (@ 11.76 GHz)	7.90	2.57×10^{-2}	3.26×10^{-3}	3.64×10^3

Table S10 Design parameters of the proposed antennas.

Symbol	Value (mm)	Symbol	Value (mm)
L_1	50.00	h	3.71
D	9.08	t	0.035
w	2.00	sub_h	1.575
l	8.70	L_2	76.00
l_{part-1}	11.20	L_3	19.00
l_{part-2}	9.50	W	54.00
l_{part-3}	5.50	l_{part-4}	6.20
w_{100}	1.38	l_{part-5}	7.50
w_{71}	2.67	l_{part-6}	42.76
w_{50}	4.76	l_{part-7}	12.00
w_{35}	7.80	l_{part-8}	2.50